

TOSHIBA RECTIFIER SILICON DIFFUSED JUNCTION TYPE

U1BC44, U1GC44, U1JC44

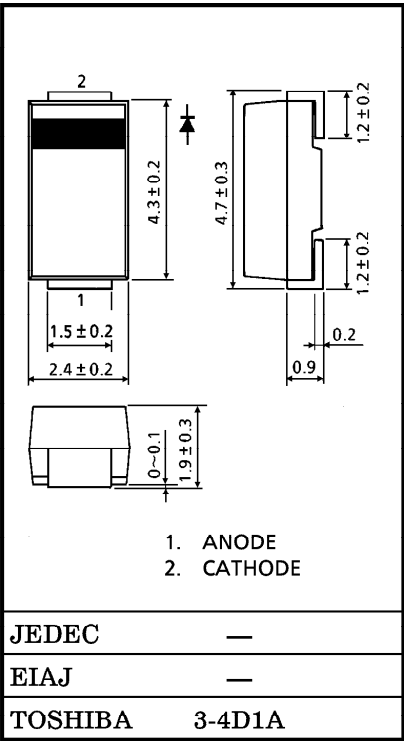
FOR HYBRID USE

Unit in mm

- Average Forward Current : $I_F(AV)=1.0A$
- Repetitive Peak Reverse Voltage : $V_{RRM}=100\sim600V$
- Mini Plastic Mold Package

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	U1BC44	V_{RRM}	100	V
	U1GC44		400	
	U1JC44		600	
Average Forward Current	On Ceramic Substrate	$I_F(AV)$	1.0 ($T_a=75^{\circ}C$)	A
	On Glass-epoxy Substrate		0.9 ($T_a=25^{\circ}C$)	
Peak One Cycle Surge Forward Current (Non-Repetitive)		I_{FSM}	30 (50Hz) 33 (60Hz)	A
Junction Temperature		T_j	$-40\sim150$	$^{\circ}C$
Storage Temperature Range		T_{stg}	$-40\sim150$	$^{\circ}C$



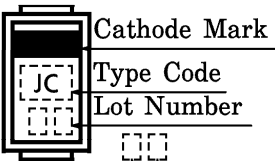
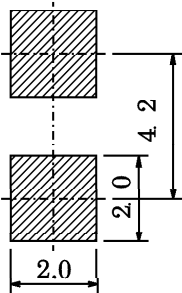
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

Weight : 0.06g

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	$I_{FM}=1.0A$		—	—	1.2	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM}=\text{Rated}$		—	—	10	μA
Thermal Resistance	$R_{th(j-a)}$	DC	On ceramic substrate	—	—	60	$^{\circ}C/W$
			On glass-epoxy substrate	—	—	120	

STANDARD SOLDERING PAD

Unit : mm

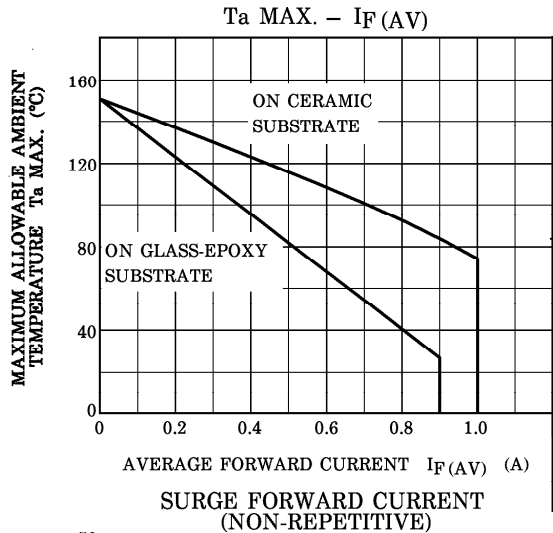
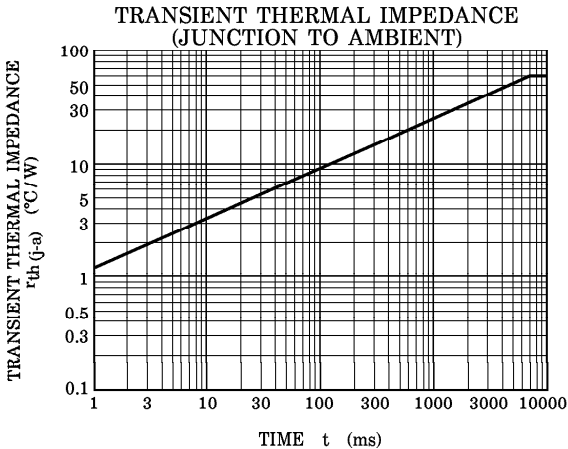
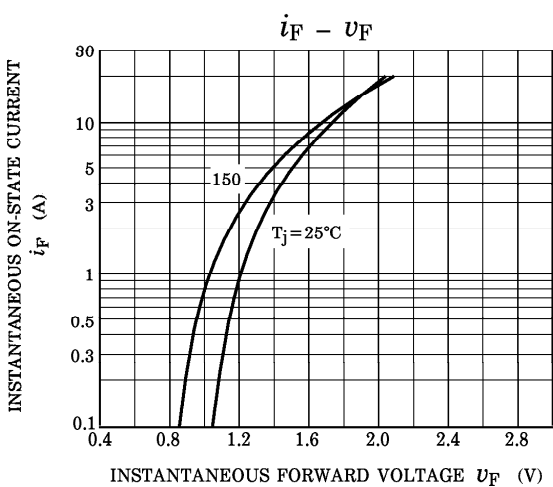


Month (Starting from Alphabet A)
Year (Last Number of the Christian Era)

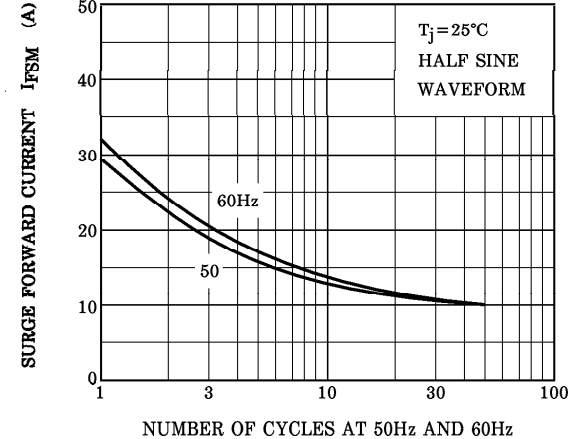
CODE	TYPE
BC	U1BC44
GC	U1GC44
JC	U1JC44

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	ON CERAMIC SUBSTRATE	ON GLASS-EPOXY SUBSTRATE
Soldering land : a □	2mm□	6mm□
Substrate size : b □	50mm□	50mm□
Substrate thickness : c □	0.64t	1.6t



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